Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC6087

Power Amplifier Applications Power Switching Applications

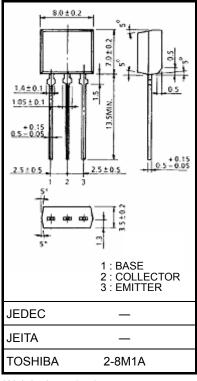
Low collector emitter saturation voltage

 $: V_{CE (sat)} = 0.5 \text{ V (max)} (I_{C} = 1A)$

High-speed switching: $t_{stg} = 0.4 \mu s$ (typ)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	160	V		
Collector-emitter voltage		V _{CEX}	160	V	
		V _{CEO}	80	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	IC	2.5	Α	
	Pulse	I _{CP}	5.0	Α	
Base current	Ι _Β	1.0	Α		
Collector power dissipation		PC	1.3	W	
Junction temperature	Tj	150	°C		
Storage temperature range		T _{stg}	-55~150	°C	



Weight:0.55g(typ)

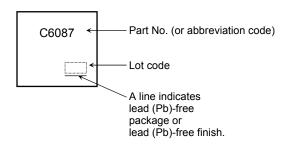
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

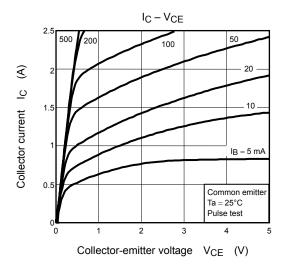
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

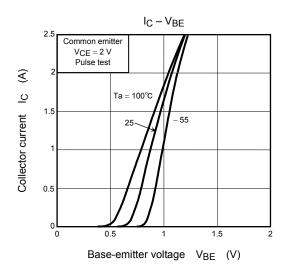
Electrical Characteristics (Ta = 25°C)

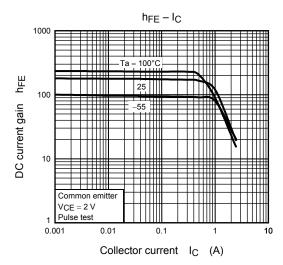
Characteristic		Symbol	Test Conditions	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	V _{CB} = 160 V, I _E = 0	_	_	1	μА
Emitter cut-off current		I _{EBO}	V _{EB} = 7 V, I _C = 0	-	_	1	μА
Collector-emitter breakdown voltage		V (BR) CEO	I _C = 10 mA, I _B = 0	80	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 1 mA	80	_	200	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 0.5 A	100	_	_	
		h _{FE (3)}	V _{CE} = 2 V, I _C = 1 A	60	_	_	
Collector emitter saturation voltage		V _{CE} (sat) (1)	I _C = 0.5 A, I _B = 50 mA	_	_	0.3	V
		V _{CE} (sat) (2)	I _C = 1 A, I _B = 100 mA	_	_	0.5	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 1 A, I _B = 100 mA	-	_	1.5	V
Transition frequency		f _T	V _{CE} = 2 V, I _C = 0.5 A	_	150	_	MH_Z
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0,f = 1MH _Z	_	14	_	pF
Switching time	Rise time	t _r	20 μ s Input $\stackrel{ _{B1}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B1}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B1}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B1}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ $\stackrel{ _{B2}}{\longrightarrow}$ Duty cycle \leq 1%	_	0.05	_	
	Storage time	t _{stg}		_	0.4	_	μS
	Fall time	t _f		_	0.15	_	

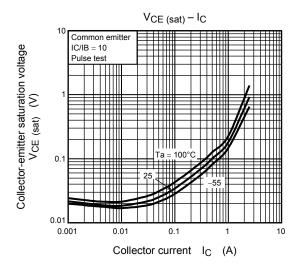
Marking

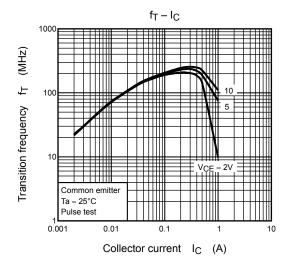


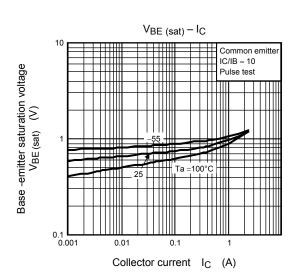


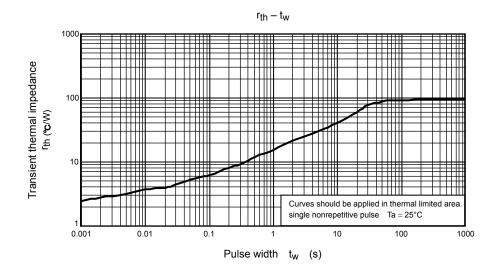


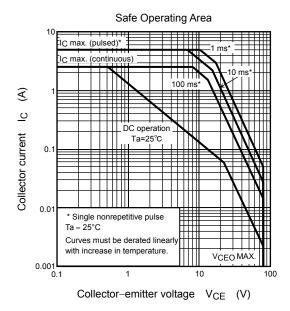












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